TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS -H)

TPCC8006-H

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q_{SW} = 7.4 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS (ON)} = 6.5 \text{ m}\Omega \text{ (typ.) (V}_{GS} = 4.5 \text{ V)}$

- High forward transfer admittance: |Yfs| = 67 S (typ.)
- Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 30 V)
- Enhancement mode: $V_{th} = 1.3$ to 2.3 V ($V_{DS} = 10$ V, $I_{D} = 0.2$ mA)

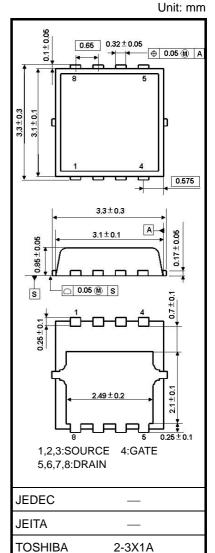
Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage (R	GS = 20 kΩ)	V_{DGR}	30	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC (Note 1)	I _D	22	А
Diain current	Pulsed (Note 1)	I _{DP} 66 P _D 27 P _D 1.9	A	
Drain power dissipati	on (Tc = 25)	P_{D}	27	W
Drain power dissipation	on (t = 10 s) (Note 2a)	P_{D}	1.9	W
Drain power dissipati	on (t = 10 s) (Note 2b)	P _D	0.7	W
Single-pulse avalance	ne energy (Note 3)	E _{AS}	126	mJ
Avalanche current		I _{AR}	22	Α
Repetitive avalanche (To	energy c = 25) (Note 4)	E _{AR}	1.89	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature	range	T _{stg}	-55 to 150	°C

Note: For Notes 1 to 4, refer to the next page.

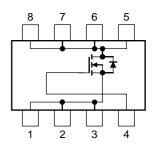
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

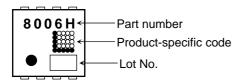
Circuit Configuration



Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25)	R _{th (ch-c)}	4.7	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	66	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2b)	R _{th (ch-a)}	180	°C/W

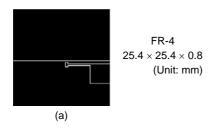
Marking (Note 5)

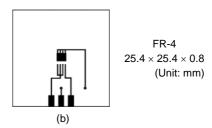


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

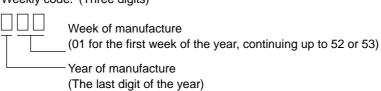




Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 200 μ H, R_G = 25 Ω , I_{AR} = 22 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



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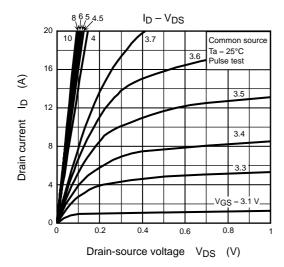
Electrical Characteristics (Ta = 25°C)

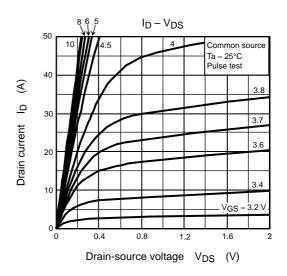
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	nt	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V		_	10	μА
Drain agurag bro	akdowa voltogo	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	±100 10	V	
Drain-source breakdown voltage		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_		_
Gate threshold vo	oltage	V _{th}	$V_{DS} = 10 \text{ V}, I_{D} = 0.2 \text{ mA}$	1.3	_	2.3	V
Drain course ON	rocistanco	Pro (OLI)	V _{GS} = 4.5 V, I _D = 11 A	_	6.5	9.3	m 0
Drain-source ON-resistance		KDS (ON)	V _{GS} = 10 V, I _D = 11 A	_	5.3	8.0	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 11 A	34	67	_	S
Input capacitance)	C _{iss}		_	1700	2200	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	110	180	pF
Output capacitance		C _{oss}		_	350	_	
Gate resistance		rg	V _{DS} = 10 V, V _{GS} = 0 V, f = 5 MHz	_	2.8	4.2	Ω
	Rise time	t _r	10 V 🗍 In = 11 A	_	3.8	_	
Switching time	Turn-on time	$\begin{array}{c} V_{\text{(BR) DSS}} & I_{D} = 10 \text{ mA, } V_{\text{GS}} = 0 \text{ V} \\ V_{\text{(BR) DSX}} & I_{D} = 10 \text{ mA, } V_{\text{GS}} = -20 \text{ V} \\ V_{\text{IS}} & V_{\text{IS}} = 10 \text{ V, } I_{D} = 0.2 \text{ mA} \\ V_{\text{GS}} = 10 \text{ V, } I_{D} = 0.2 \text{ mA} \\ V_{\text{GS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{GS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{GS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{CS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{DS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{DS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{DS}} = 10 \text{ V, } I_{D} = 11 \text{ A} \\ V_{\text{CS}} = 0 \text{ V, } I_{D} = 11 \text{ A} \\ V_{C$	_				
Switching time	Fall time	t _f	2.7.9 W W V V V V V V V V V V V V V V V V V	_	9.7	9.3 r 8.0	ns
	Turn-off time	t _{off}		_	42	_	
Total gate charge	;	V _{DD} ≈ 24 V, V _{GS} = 10 V, I _D = 22 A — 27 -		_			
(gate-source plus	gate-drain)	Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 22 \text{ A}$	_			
Gate-source charge 1		Q _{gs1}		_	5.2	_	nC
Gate-drain ("Miller") charge		Q _{gd}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$	_	4.8	_	
Gate switch char	ge	Q _{SW}	1	_	7.4	_	

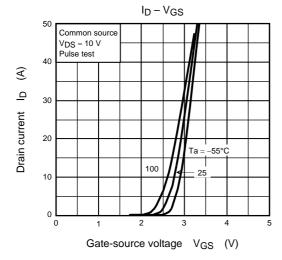
Source-Drain Ratings and Characteristics (Ta = 25°C)

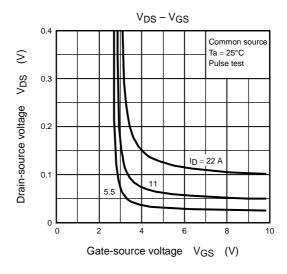
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I _{DRP}	_	_	_	66	Α
Forward voltage (diode)			V _{DSF}	$I_{DR} = 22 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

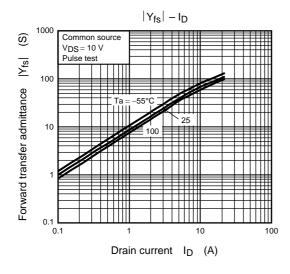
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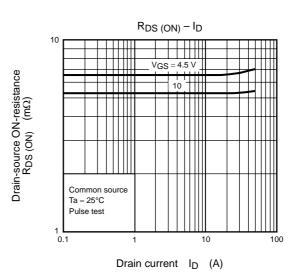




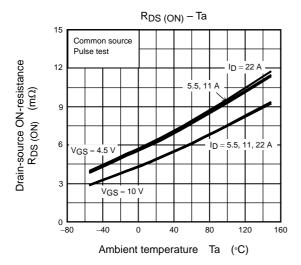


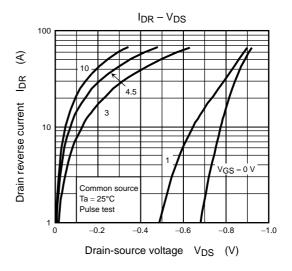


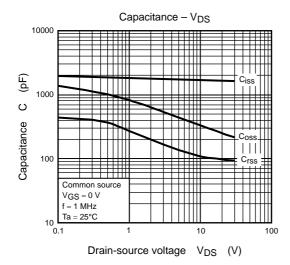


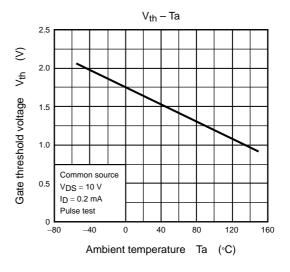


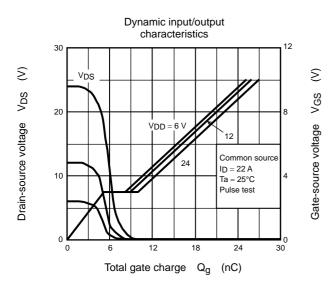
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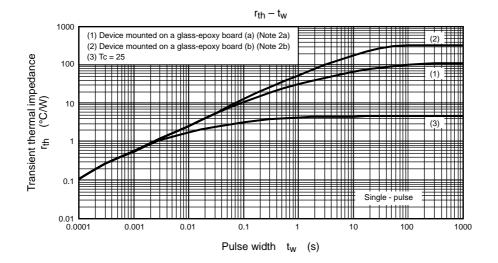


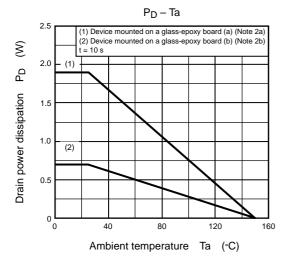


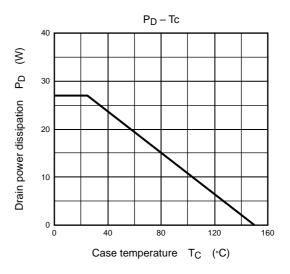


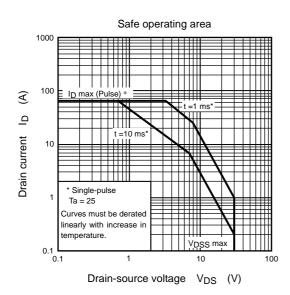


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